AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-4. (canceled)

5. **(currently amended)** A GaN light emitting diode, comprising:

a first conductive GaN clad layer which is a GaN crystalline layer doped with an n-type impurity;

~~with an upper surface provided with~~ a first contact formed ~~thereon~~ on and in direct contact with an upper surface of the first conductive GaN clad layer;

an active layer formed on a lower surface of the first conductive GaN clad layer;

a second conductive GaN clad layer formed on a lower surface of the active layer, wherein the second conductive GaN clad layer is a GaN crystalline layer doped with a p-type impurity;

a conductive adhesive layer formed [[on]] below the second conductive GaN clad layer; [[and]]

a conductive substrate ~~, with a lower surface provided with a second contact formed thereon,~~ formed on a lower surface of the conductive adhesive layer; and [[,]]

a second contact formed on a lower surface of said conductive substrate;

wherein the conductive adhesive layer is made of a material selected from the group consisting of Au-Sn, Sn, In, Au-Ag and Pb-Sn.

6-23. (canceled)

24. **(new)** The GaN light emitting diode as set forth in claim 5, further comprising a reflective layer made of a conductive material and formed between the second conductive GaN clad layer and the conductive adhesive layer.

25. **(new)** The GaN light emitting diode as set forth in claim 24, wherein the reflective layer is made of a material selected from the group consisting of Au, Ni, Ag, Al and alloys thereof.

26. **(new)** The GaN light emitting diode as set forth in claim 5, wherein the conductive substrate is made of a material selected from the group consisting of silicon (Si), germanium (Ge) and GaAs.